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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **Kenji MARUYAMA et al.**

Group Art Unit: 2813

Serial No.: 09/960,296

Examiner: **Laura M. Schillinger**

Filed: **September 24, 2001**

**P.T.O. Confirmation No.: 4754**

For: **SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME**

**AMENDMENT ACCOMPANYING RCE**

Commissioner for Patents  
Washington, D.C. 20231

January 23, 2003

Sir:

Applicants submit the following Amendment to accompany the RCE filed herewith.

**IN THE CLAIMS:**

**Please amend claims 1 and 16 as follows:**

SUB  
B1  
A1

1. (Amended) A semiconductor device comprising a first electrode, a ferroelectric film formed above the first electrode, and a second electrode formed above the ferroelectric film, further comprising

an intermediate layer of perovskite crystal structure formed at least one of boundary between the first electrode and the ferroelectric film, and boundary between the ferroelectric film and the second electrode, materials of the intermediate layer being different from materials of the first electrode, the second electrode and the ferroelectric film.

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